

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
S8	3831	(flash near3 memory) with (isolat\$3 isolat\$3 near3 trench trench hole recess opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:16
S9	2971	S8 and (mask\$3 resist etch\$3 pattern\$3) with (isolat\$3 isolat\$3 near3 trench trench hole recess opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:17
S10	1200	S9 and (insulat\$4 dielectric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S11	1112	S10 and (oxide nitride pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:09
S12	1029	S11 and (substrate wafer) with (isolat\$3 isolat\$3 near3 trench trench hole recess opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:10
S13	129	S12 and sacrificial	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:10
S14	912	S12 and floating	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:11
S15	899	S12 and control	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:12
S17	789	S15 and (conduct\$3 metal\$6)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S18	465	S17 and self adj align\$5	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:19

S19	465	S18 and gate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:14
S20	369	S19 and tunnel\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:20
S21	30324	((floating control) near3 gate) same (isolat\$3 isolat\$3 near3 trench trench hole recess opening via groove)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:17
S22	6605	S21 and (mask\$3 resist etch\$3 pattern\$3) with (isolat\$3 isolat\$3 near3 trench trench hole recess opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S23	7663	S21 and (mask\$3 resist etch\$3 pattern\$3) with (isolat\$3 isolat\$3 near3 trench trench hole recess opening groove via)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S24	6455	S23 and (insulat\$4 dielectric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S25	5879	S24 and (conduct\$3 metal\$6)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:18
S26	2887	S25 and self adj align\$5	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:19
S27	1830	S26 and tunnel\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/20 18:20

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L12	12	((floating control) near3 gate) same (isolat\$3 isolat\$3 near3 trench) with (trench hole recess opening via groove) with sacrificial.clm.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/21 07:45